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Unit: mm

TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (Four Darlington Power Transistors in One)

# **MP4021**

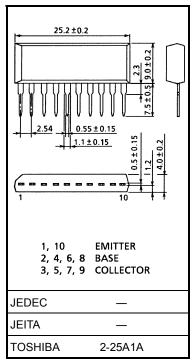
#### High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation) :  $P_T = 4 W (T_a = 25^{\circ}C)$
- High collector current: I<sub>C</sub> (DC) = 2 A (max)
- High DC current gain:  $h_{FE} = 2000 \text{ (min)} (V_{CE} = 2 \text{ V}, I_C = 1 \text{ A})$
- Zener diode included between collector and base.

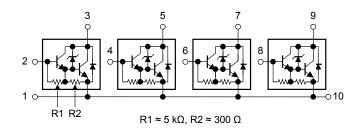
#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	85	V	
Collector-emitter voltage		V <sub>CEO</sub>	100 ± 15	V	
Emitter-base voltage		V <sub>EBO</sub>	8	V	
	DC	Ι <sub>C</sub>	2	A	
Collector current	Pulse	I <sub>CP</sub>	3		
Continuous base current		Ι <sub>Β</sub>	0.5	А	
Collector power dissipation (1-device operation)		P <sub>C</sub>	2.0	W	
Collector power dissipation (4-device operation)		PT	4.0	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 2.1 g (typ.)

## **Array Configuration**



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Industrial Applications

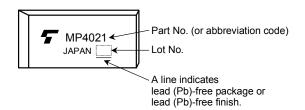
### **Thermal Characteristics**

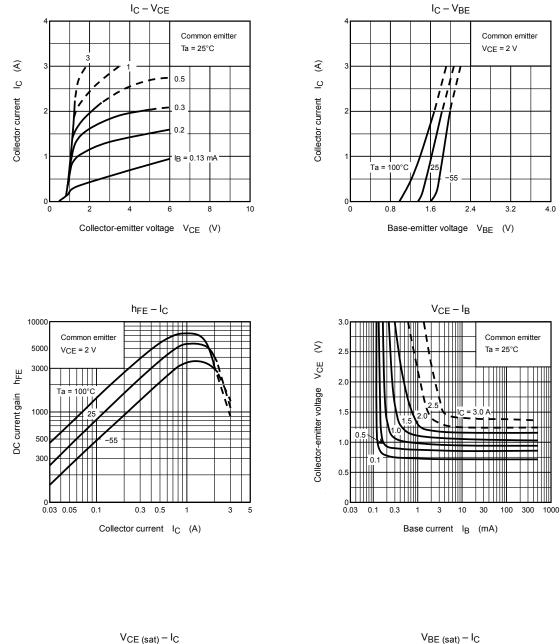
Characteristics	Symbol	Max	Unit	
Thermal resistance from junction to ambient	ΣR <sub>th (j-a)</sub>	31.3	°C/W	
(4-device operation, Ta = 25°C)				
Maximum lead temperature for soldering purposes	TL	260	°C	
(3.2 mm from case for 10 s)				

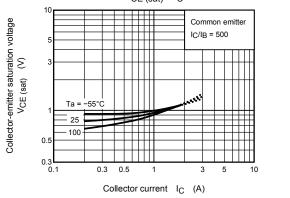
# Electrical Characteristics (Ta = 25°C)

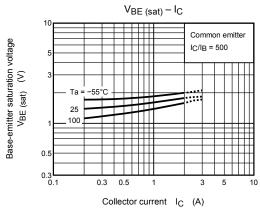
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	V <sub>CB</sub> = 80 V, I <sub>E</sub> = 0 A	_	—	10	μA
Collector cut-off current		ICEO	V <sub>CE</sub> = 80 V, I <sub>B</sub> = 0 A	_	_	10	μA
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 8 V, I <sub>C</sub> = 0 A	0.8	_	4.0	mA
Collector- emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>E</sub> = 0 A	85	100	115	V
DC current gain		h <sub>FE</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 1 A	2000	_	_	-
Saturation voltage	Collector-emitter	V <sub>CE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 1 mA	_	_	1.5	v
	Base-emitter	V <sub>BE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 1 mA	_	_	2.0	
Transition frequency		fT	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	_	100	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0 A, f = 1 MHz	_	20	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$Input \xrightarrow{I_{B1}} Output$ $20 \ \mu s \qquad I_{B2} \qquad \bigvee \qquad V_{CC} = 30 \ V$ $I_{B1} = -I_{B2} = 1 \ \text{mA, duty cycle} \le 1\%$	_	0.45	_	μs
	Storage time	t <sub>stg</sub>		_	2.0	_	
	Fall time	t <sub>f</sub>		_	0.4	—	

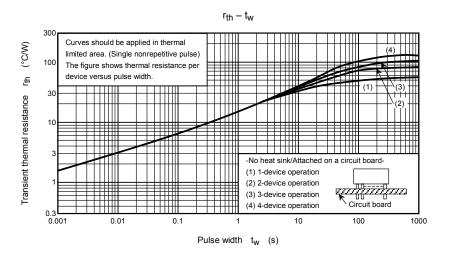
### Marking

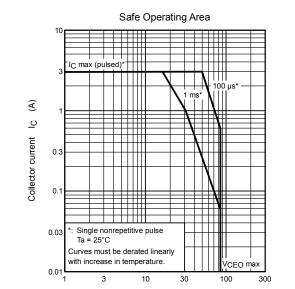






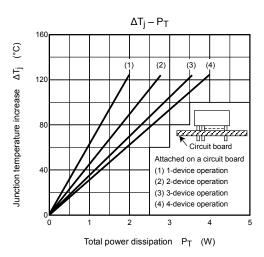






Collector-emitter voltage V<sub>CE</sub> (V)

P<sub>T</sub> – Ta (1) 1-device operation (2) 2-device operation Ś (3) 3-device operation (4) 4-device operation Ł Attached on a circuit board (4) Circuit board (3) (2) (1) 0L 0 40 80 120 160 200 Ambient temperature Ta (°C)



Total power dissipation

4

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